



### P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = 25°C
	150mΩ @ V <sub>GS</sub> = -4.5V	-1.5A
-20V	200mΩ @ V <sub>GS</sub> = -2.5V	-1A
	240mΩ @ V <sub>GS</sub> = -1.8V	-0.9A

## **Description and Applications**

This MOSFET is designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

### **Features**

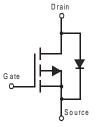
- Low On-Resistance
- Very Low Gate Threshold Voltage V<sub>GS(th)</sub> ≤ 1V
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

### **Mechanical Data**

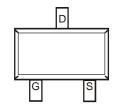
- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 ©3
- Weight: 0.006 grams (Approximate)







Internal Schematic



Top View

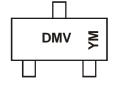
### **Ordering Information (Note 5)**

Part Number	Case	Packaging
DMP2240UWQ-7	SOT-323	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_grade\_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



DMV = Product Type Marking Code YM = Date Code Marking Y = Year (ex: B = 2014) M = Month (ex: 9 = September)

Date Code Key

Year	2014		2015	2016		2017	2018		2019	2020	)	2021
Code	В		С	D		Е	F		G	Н		
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# Maximum Ratings (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage		$V_{DSS}$	-20	V
Gate-Source Voltage		V <sub>GSS</sub>	±12	V
Drain Current (Note 6)	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	-1.5 -1.0	А
Pulsed Drain Current		I <sub>DM</sub>	-5	A

## **Thermal Characteristics**

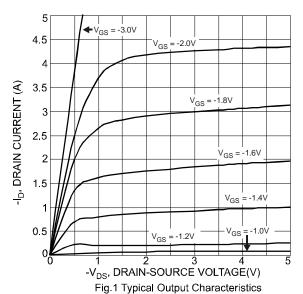
Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 6)	$P_{D}$	250	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	500	°C/W
Operating and Storage Temperature Range	$T_{J_1}T_{STG}$	-55 to +150	°C

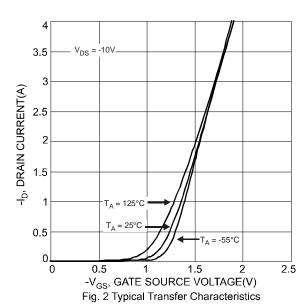
## Electrical Characteristics (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)	Symbol	IVIIII	тур	IVIAX	Oilit	rest condition	
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	T <sub>J</sub> = +25°C T <sub>J</sub> = +125°C	I <sub>DSS</sub>	_	_	-1.0 -5.0	μА	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage		I <sub>GSS</sub>	—	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage		$V_{GS(th)}$	-0.45	_	-1.0	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$
Static Drain-Source On-Resistance		R <sub>DS (ON)</sub>	_	92 134 180	150 200 240	mΩ	$V_{GS} = -4.5V$ , $I_D = -2.0A$ $V_{GS} = -2.5V$ , $I_D = -1.5A$ $V_{GS} = -1.8V$ , $I_D = -0.5A$
Forward Transconductance		g <sub>FS</sub>	_	3.1	_	S	$V_{DS} = -10V, I_D = -810mA$
Diode Forward Voltage (Note 7)		V <sub>SD</sub>	_	_	-0.9	V	$V_{GS} = 0V, I_{S} = -0.5A$
DYNAMIC CHARACTERISTICS				•			
Input Capacitance		C <sub>iss</sub>		320	_	pF	10)/ )/
Output Capacitance		Coss	_	80	_	pF	$V_{DS} = -16V, V_{GS} = 0V$ - f = 1.0MHz
Reverse Transfer Capacitance		C <sub>rss</sub>	_	60	_	pF	1 = 1.000112
Turn-On Delay Time		t <sub>D(on)</sub>	_	12.5	_	ns	
Turn-On Rise Time		t <sub>r</sub>	_	10.3	_	ns	$V_{DS} = -10V, V_{GS} = -4.5V,$
Turn-Off Delay Time		t <sub>D(off)</sub>		46.5	_	ns	$R_L = 10\Omega$ , $R_G = 1.0\Omega$
Turn-Off Fall Time	t <sub>f</sub>	_	22.2	_	ns		

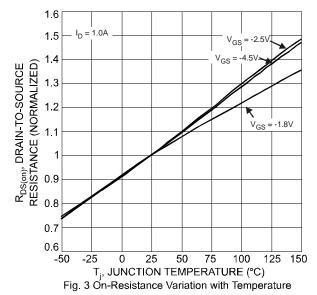
Notes:

- 6. Device mounted on FR-4 substrate PC board, 2oz. Copper, with minimum recommended pad layout.
- 7. Short duration pulse test used to minimize self-heating effect.









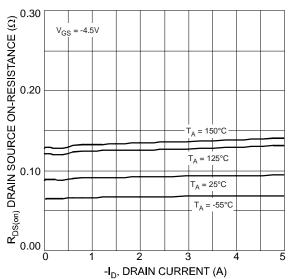
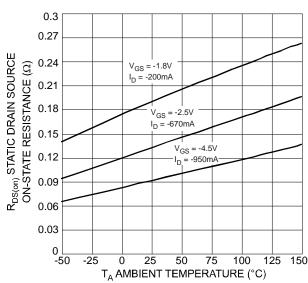


Fig. 5 Drain-Source On-Resistance

Vs. Drain Current and Temperature





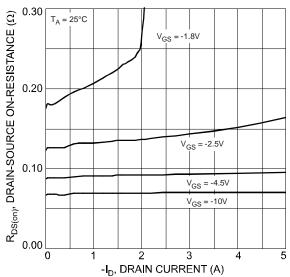
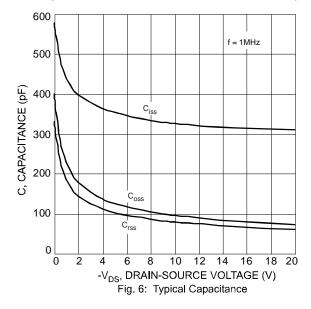


Fig. 4 On-Resistance vs Drain Current and Gate Voltage



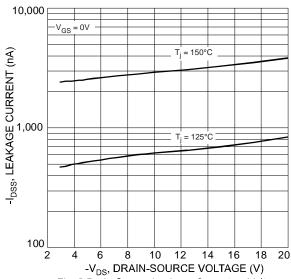
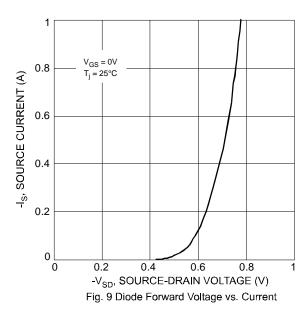


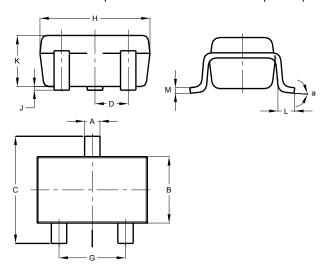
Fig. 8 Drain-Source Leakage Current vs Voltage





# **Package Outline Dimensions**

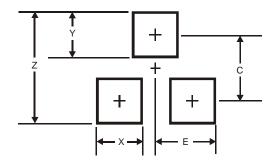
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT323							
Dim	Min	Max	Тур				
Α	0.25	0.40	0.30				
В	1.15	1.35	1.30				
С	2.00	2.20	2.10				
D	0.	.650 BS	С				
F	0.375	0.475	0.425				
G	1.20	1.40	1.30				
H	1.80	2.20	2.15				
J	0.00	0.10	0.05				
K	0.90	1.00	0.95				
L	0.25	0.40	0.30				
M	0.10	0.18	0.11				
а	8°C						
All Dimensions in mm							

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.8
Х	0.7
Y	0.9
С	1.9
E	1.0



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